# 1. General description

NPN high power bipolar transistor in a power DPAK, TO-252 (SOT428C) Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- High thermal power dissipation capability
- · High energy efficiency due to less heat generation
- High current gain at V<sub>CE</sub> = 60 V
- Electrically similar to popular MJD31 series
- Low collector emitter saturation voltage
- Fast switching speeds
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Power management
- Load switch
- · Linear mode voltage regulator
- · Constant current drive backlighting application
- Motor drive
- · Relay replacement

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	100	V
I <sub>C</sub>	collector current		-	-	3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	5	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 60 V; $I_{C}$ = 20 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	120	-	-	
		$V_{CE}$ = 4 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ = 300 µs; $\delta \leq 0.02$ ; $T_{amb}$ = 25 °C	25	-	-	
		$V_{CE}$ = 4 V; $I_{C}$ = 3 A; continuous; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	10	-	-	



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	
2	С	collector		Ę
3	Е	emitter		в - [
mb	С	mounting base; connected to collector	1 3	C; mb aaa-029889
			DPAK (SOT428C)	

## 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
MJD31CH-Q		Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428C			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
MJD31CH-Q	MJD31CAH

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC601134).

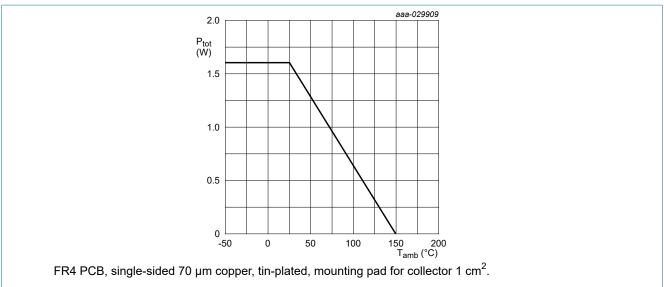
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	100	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	5	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C	[1]	-	15	W
		T <sub>amb</sub> ≤ 25 °C	[2]	-	1.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Total power dissipation junction to mounting base.

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<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

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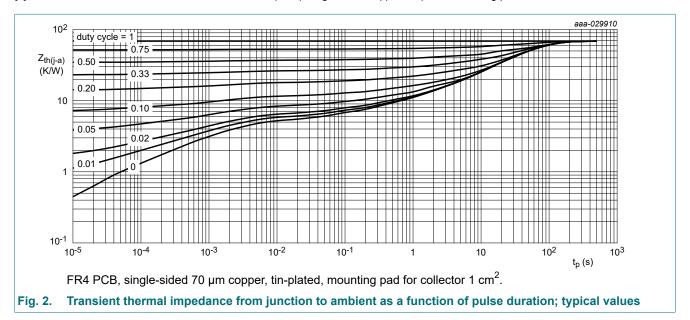
### Fig. 1. Power derating curves SOT428C

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	79	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	9	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.



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### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CES</sub>	collector-emitter cut-off	V <sub>CE</sub> = 80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	1	μΑ
	current	V <sub>CE</sub> = 64 V; V <sub>BE</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	1	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 60 V; $I_{C}$ = 20 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	120	-	-	
		$V_{CE}$ = 4 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	-	-	
		$V_{CE}$ = 4 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ = 300 μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	25	-	-	
		$V_{CE}$ = 4 V; $I_{C}$ = 3 A; continuous; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	10	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 3 A; $I_B$ = 375 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	1.2	V
$V_{BE}$	base-emitter voltage	$V_{CE}$ = 4 V; $I_{C}$ = 3 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	1.8	V
h <sub>fe</sub>	small-signal current gain	$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; f = 1 kHz; pulsed; $t_{p} \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	20	-	-	
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 500 \text{ mA}; f = 100 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$	3	-	-	MHz

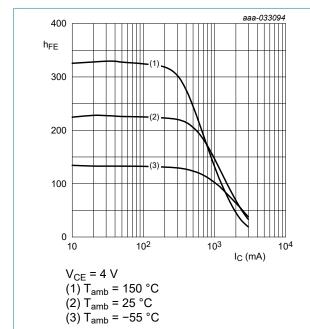


Fig. 3. DC current gain as a function of collector current; typical values

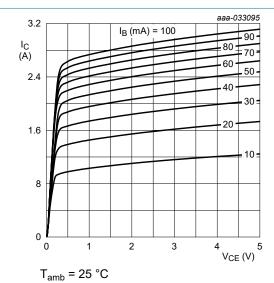


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

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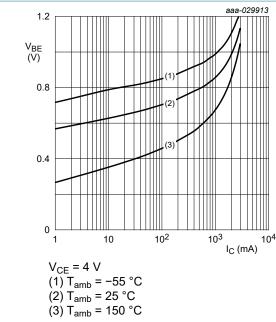
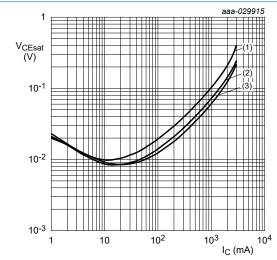


Fig. 5. Base-emitter voltage as a function of collector current; typical values



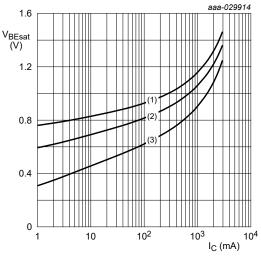
 $I_C/I_B = 10$ 

(1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

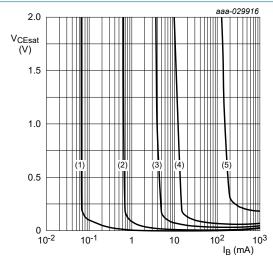
(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{C}/I_{B} = 10$ (1)  $T_{amb} = -55 \,^{\circ}C$ (2)  $T_{amb} = 25 \,^{\circ}C$ (3)  $T_{amb} = 150 \,^{\circ}C$ 

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



(1)  $I_C = 10 \text{ mA}$ 

(2)  $I_C = 100 \text{ mA}$ 

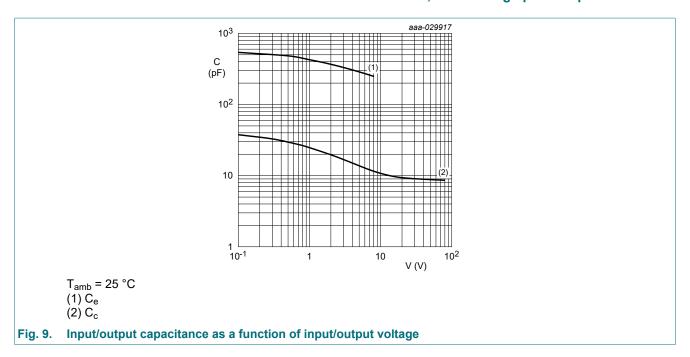
(3)  $I_C = 500 \text{ mA}$ 

 $(4) I_C = 1000 \text{ mA}$ 

 $(5) I_C = 3000 \text{ mA}$ 

Fig. 8. Collector-emitter saturation region as a function of base current; typical values

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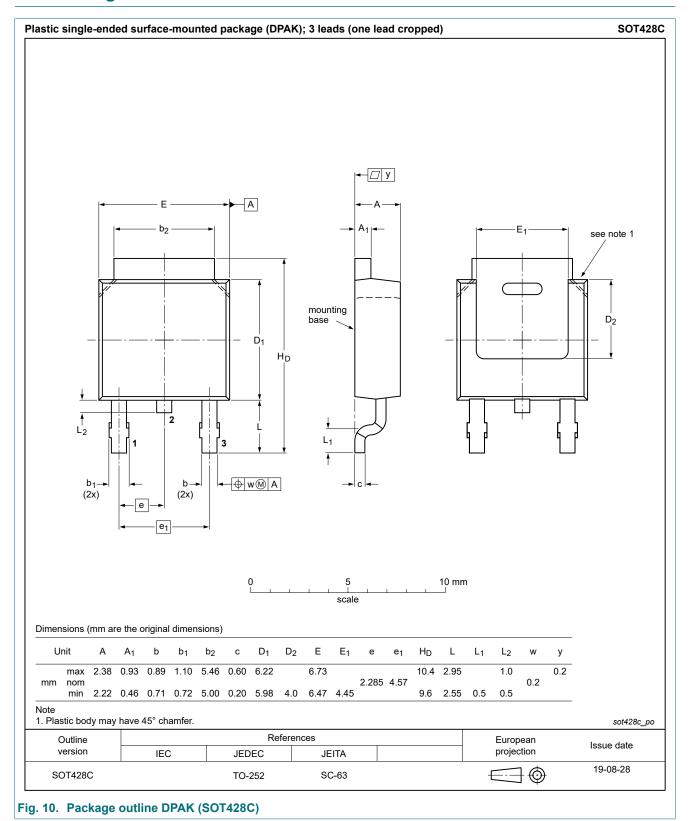
## 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

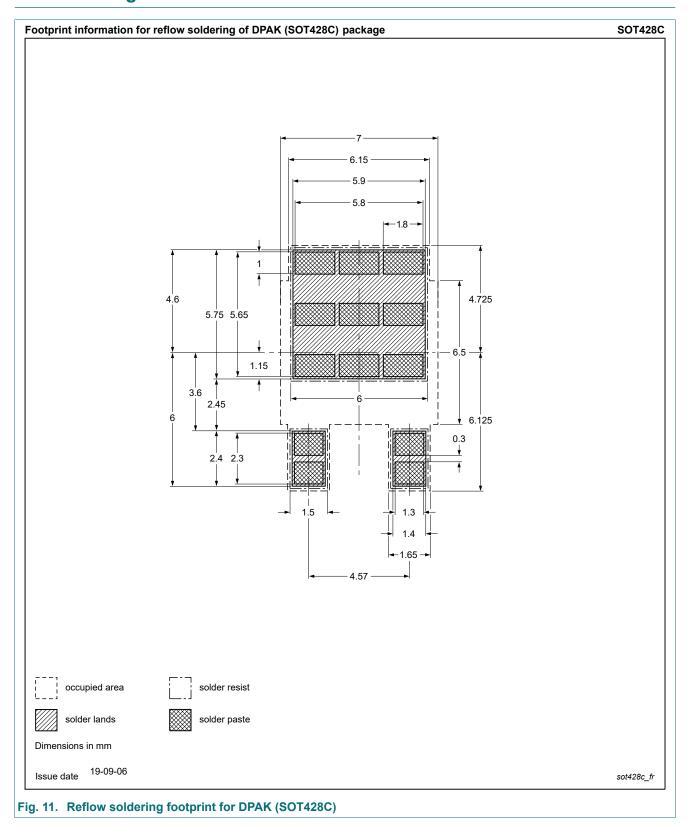
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# 12. Package outline



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# 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

	· J						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
MJD31CH-Q v.3	20210518	Product data sheet	-	MJD31CH-Q v.2			
Modifications:	<ul> <li>Features and benefit</li> </ul>	Features and benefits: added recommendation for automotive applications					
MJD31CH-Q v.2	20210303	Product data sheet	-	MJD31CH-Q v.1			
MJD31CH-Q v.1	20210126	Objective data sheet	-	-			

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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